IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:	
CHAN WOO PARK, ET AL.	Art Group:
Application No.:	Examiner:
Filed:	
For: **Self-Aligned Heterojunction Bipolar Transistor and Manufacturing Method Thereof**	

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Date: 10/1/03

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Information Disclosure Statement

New U.S. Patent Application for
SELF-ALIGNED HETEROJUNCTION BIPOLAR TRANSISTOR AND MANUFACTURING METHOD THEREOF
Our Ref. No.: P02EC048/US/jy

Reference No.:

(1) High-Performance SiGe Epitaxial Base Bipolar Transistors Produced by a Reduced-Pressure CVD Reactor
(IEEE ELECTRON DEVICE LETTERS, VOL. 14, NO. 9, SEPTEMBER 1993, Pages 450-452)

(2) 75-GHz f_T SiGe-Base Heterojunction Bipolar Transistors
(IEEE ELECTRON DEVICE LETTERS, VOL. 11, NO. 4, APRIL 1990, Pages 171-173)

(3) Sub-20 ps ECL Circuits with High-Performance Super Self-Aligned Selectively Grown SiGe Base (SSSB) Bipolar Transistors
(IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. 42, NO. 3, MARCH 1995, Pages 483-488)

(4) Vertical Profile Optimization of Very High Frquency Epitaxial Si- and SiGe-Base Bipolar Transistors *(0-7803-1450-6, 1993 IEEE)*

(5) A High-Speed Low $1/f$ Noise SiGe HBT Technology Using Epitaxially-Aligned Polysilicon Emitters
(IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. 46, NO. 7, JULY 1999, Pages 1525-1531)

(6) US Patent No. 6,384,469
(7) US Patent No. 5,296,391
(8) US Patent No. 5,059,544
(9) US Patent No. 5,506,427
(10) JP Laid-Open No. 2000-243860
(11) JP Laid-Open No. 10-261650

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

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Complete if Known	
Application Number	
Filing Date	
First Named Inventor	Chan Woo Park
Art Unit	
Examiner Name	
Attorney Docket Number	51876P386

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number - Kind Code[2] *(if known)*	Publication Date or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US-6384469	05-07-2002	Chantre	
		US-5296391	03-22-1994	Sato et al.	
		US-5059544	10-22-1991	Burghartz et al.	
		US-5506427	04-09-1996	Imai	
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3] - Number[4] - Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
		2000-243860	09-08-2000	Hitachi Ltd.		
		10-261650	09-29-1998	Sony Corp.		

Examiner Signature		Date Considered	

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

[1]Applicant's unique citation designation number (optional). [2]See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached.

Based on PTO/SB/08A (08-03) as modified by Blakely, Sokoloff, Taylor & Zafman (wlr) 08/11/2003.

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Application Number	
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First Named Inventor	Chan Woo Park
Art Unit	
Examiner Name	
Attorney Docket Number	51876P386

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
		"High-Performance SiGe Epitaxial BAse Bipolar Transistors Produced by a Reduced-Pressure CVD Reactor", IEEE Electron Device Letters, Vol. 14, No. 9, Sept. 1993, pages 450-452	
		"75-GHz f SiGe-Base Heterjunction Bipolar Transistors", IEEE Electron Device Letters, Vol. 11, No. 4, April 1990, pages 171-173	
		"Sub-20 ECL Circuits with High-Performance Super Self-Aligned Selectively Grown SiGe Bse (SSSB) Bipolar Transistors", IEEE Transactions on Electron Devices, Vol. 42, No. 3, March 1995, pages 483-488	
		"Vertical Profile Optimization of Very High Frequency Epitaxial Si-and SiGe-Base Bipolar Transistors", 1993 IEEE, 0-7803-1450-6	
		"A High-Speed Low 1/f Noise SiGe HBT Technology Using Epitaxially-Aligned Polysilicon Emitters", IEEE Transactions on Electron Devices, Vol. 46, No. 7, July 1999, Pages 1525-1531	

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